

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	111552	semiconductor adj device and gate	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2006/03/03 09:51
L2	106089	1 not (@rlad>"20040830" @ad>"20040830")	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2006/03/03 09:56
L3	19873	2 and gate adj (oxide dioxide dielectric insulat\$3) same (heat\$3 thermal\$2 anneal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/03 09:57
L4	2955	3 and (vacuum vacuum pressure) with (heat\$3 thermal\$2 anneal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/03 09:59
L5	10	4 and (vacuum vacuum low near3 pressure) with (pre preliminary) adj2 (heat\$3 thermal\$2 anneal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/03 10:00
L6	10	5 and (pre preliminary) adj2 (heat\$3 thermal\$2 anneal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/03 10:00